Diode Semiconductor Device - Page 1 of 1



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Inclosure Material:

Ceramic

Overall Length:

3.040 millimeters

Terminal Length:

2.040 millimeters

Overall Height:

1.110 millimeters

Overall Width:

2.500 millimeters

Mounting Facility Quantity:

3

Mounting Method:

Compression

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

250.0 reverse voltage, instantaneous

Current Rating Per Characteristic:

200.00 milliamperes source cutoff current preset and 625.00 milliamperes repetitive peak forward current universal

Power Rating Per Characteristic:

225.0 milliwatts small-signal input power, common-emitter peak

Capacitance Rating In Picofarads:

5.0

Maximum Operating Tempurature Per Measurement Point:

150.0 degrees celsius junction and -55.0 degrees celsius junction

Terminal Type And Quantity:

3 tab, solder lug

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:
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No

Fiig:

A110a0